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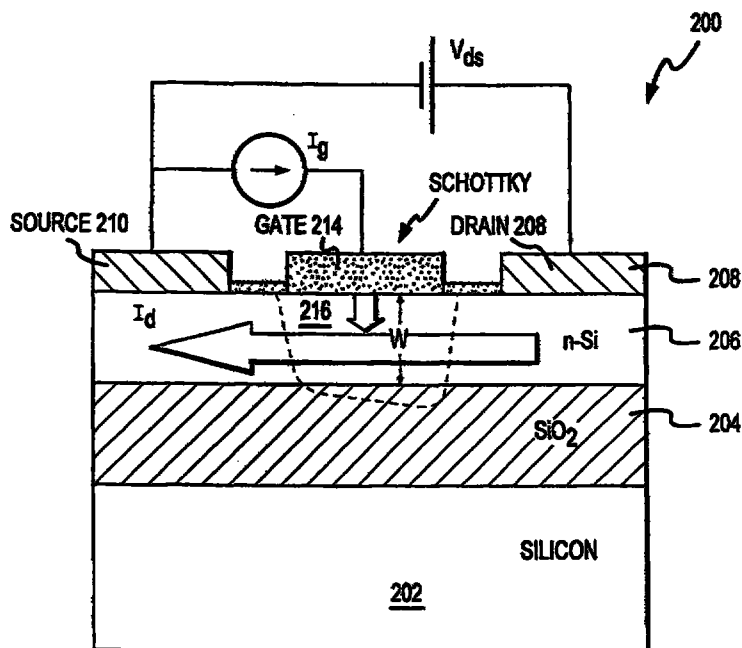
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(54) Title: **CURRENT CONTROLLED FIELD EFFECT TRANSISTOR**



(57) Abstract: Various embodiments include a transistor device that is controlled by a gate current and that exhibits low power consumption as well as high speed characteristics. In various embodiments, an enhancement mode MESFET device exhibits channel drain current that is controlled by the application of bias current into the gate. Complementary n- and p-channel devices can be realized for, for example, micropower analog and digital circuit applications.

WO 00/74144 A1